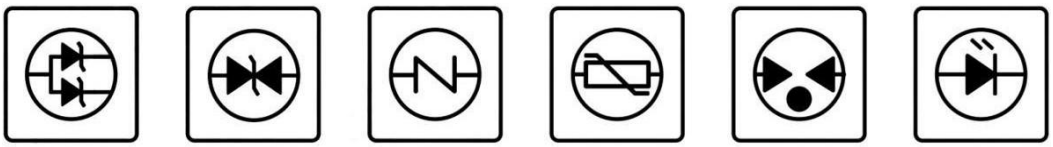
MSKSEMI 美森科
SEMICONDUCTOR



MJD122(MS)

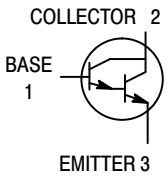
Product specification

TRANSISTOR（NPN）

FEATURES

- High DC Current Gain
- Electrically Similar to Popular TIP122
- Built-in a Damper Diode at E-C

Reference News

PACKAGE OUTLINE	Pin Configuration	Marking
 1.BASE 2.COLLECTOR 3.EMITTER		MSKSEMI MJD122 MS XXX

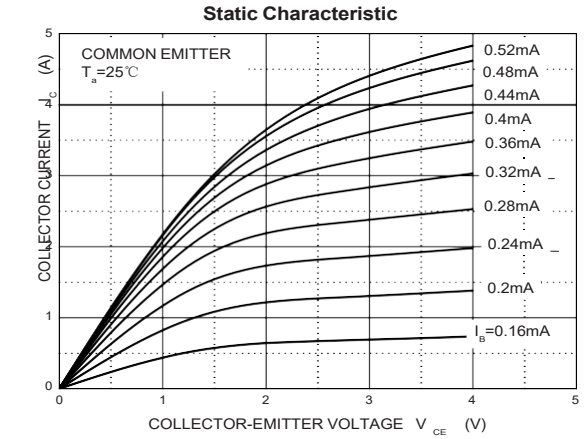
MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

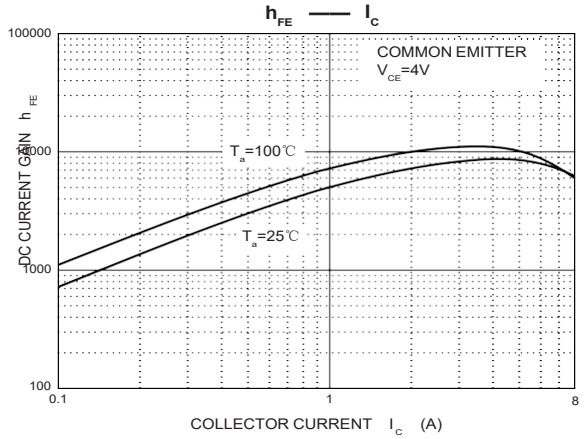
Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-EmitterVoltage	-100	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-6	A
I_{CP}^*	Collector Current -Pluse	-10	A
P_C	Collector Power Dissipation	1.25	W
T_J,T_{stg}	Operating Junction and Storage Temperature Range	-55-150	℃

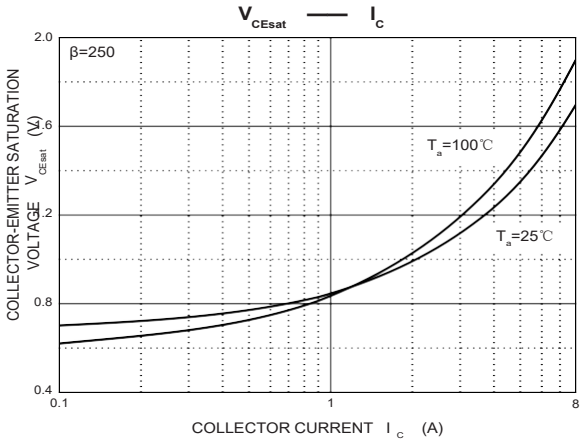
ELECTRICAL CHARACTERISTICS(T_a=25℃ unless otherwise specified)

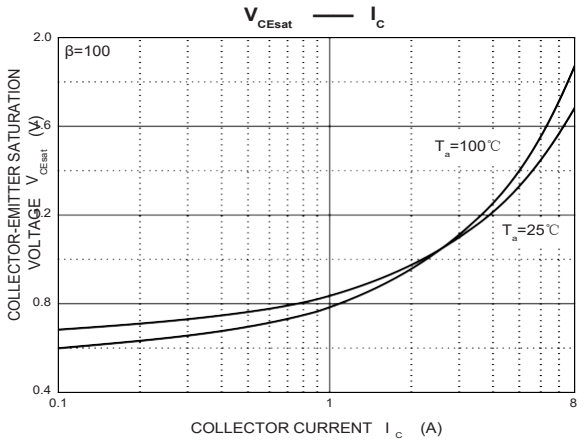
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic=1mA,I_E=0	100			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic=30mA,I_B=0	100			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=3mA,I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}= 100V,I_E=0			10	μA
Collector-emitter cut-off current	I_{CEO}	V_{CE}=50V,I_E=0			10	μA
Emitter cut-off current	I_{EBO}	V_{EB}=5V,I_C=0			2	mA
DC current gain	$h_{FE(2)}$	V_{CE}=4V,I_C=4A	1000		12000	
	$h_{FE(3)}$	V_{CE}=4V,I_C=8A	100			
Collector-emitter saturation voltage	$V_{CE(sat)}$(1)	I_C=4A,I_B= 16mA			2	V
	$V_{CE(sat)}$(2)	I_C=8A,I_B=80mA			4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=8A,I_B=80mA			4.5	V
Base-emitter voltage*	V_{BE}	V_{CE}=4V,I_C=4A			2.8	V
Collector output capacitance	C_{ob}	V_{CB}= 10V,I_E=0,f=0.1MHz			200	pF

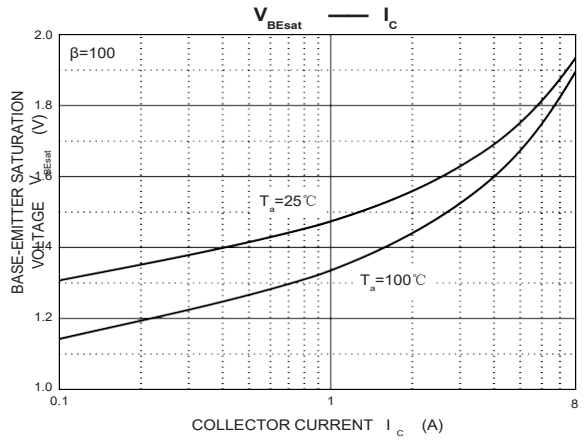
TypicalCharacterisitics

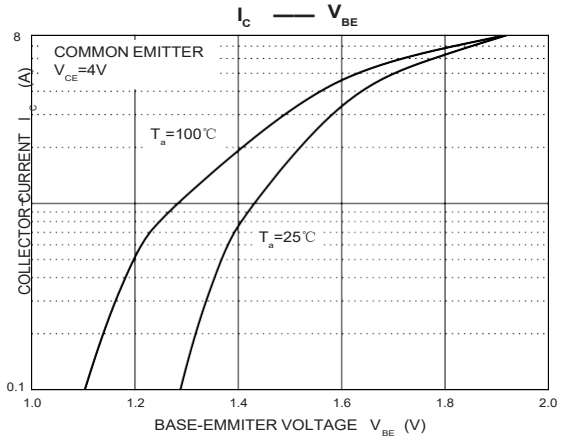


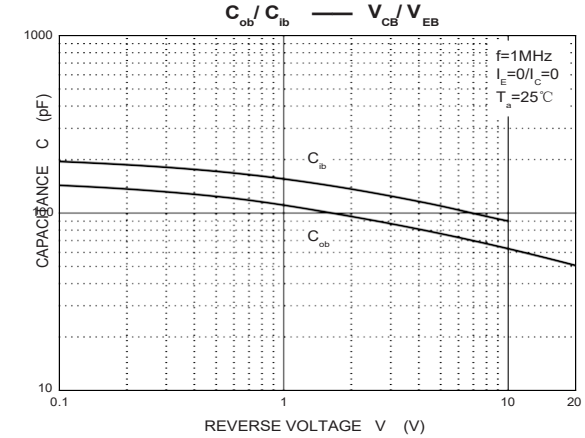


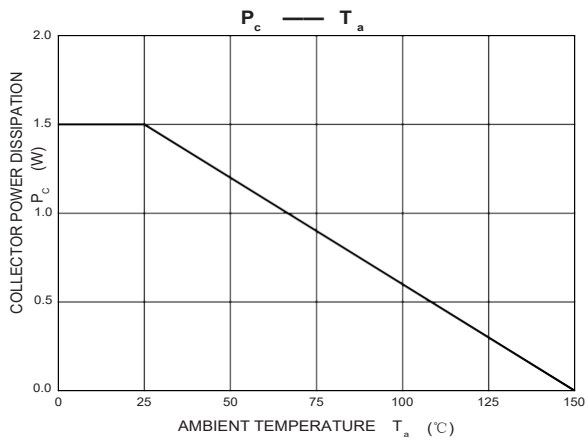




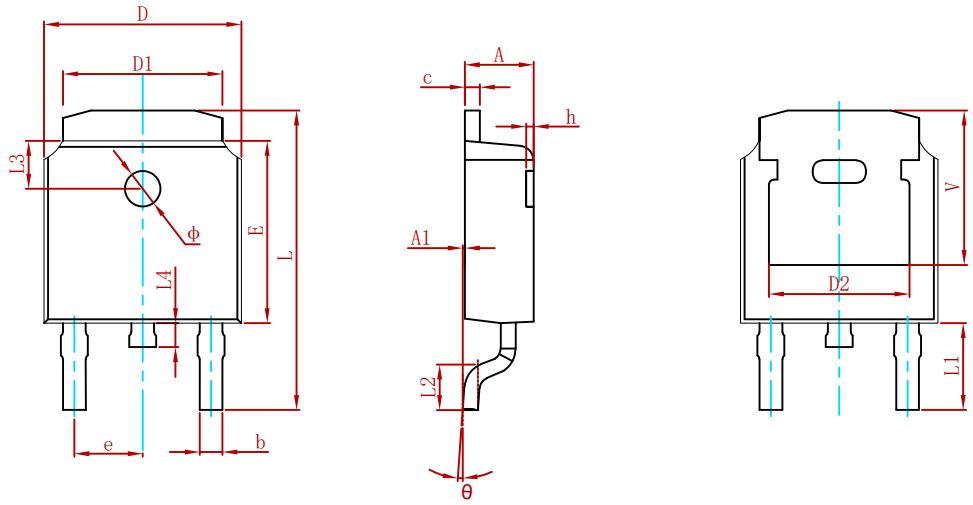






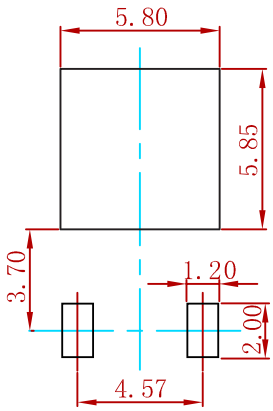


PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	

Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.05mm.
3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
MJD122(MS)	TO-252	2500

Attention

■ Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.

■ MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specificationsof any andall MSKSEMI Semiconductor products described orcontained herein.

■ Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer'sproducts orequipment.

■ MSKSEMI Semiconductor. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with someprobability. It is possiblethat these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits anderror prevention circuitsfor safedesign, redundant design, and structural design.

■ In the event that any or all MSKSEMI Semiconductor products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from theauthorities concerned in accordance with the above law.

■ No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.

■ Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringementsof intellectual property rights or other rightsof third parties.

■ Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. Whendesigning equipment, referto the "Delivery Specification" for the MSKSEMI Semiconductor productthat you intend to use.